

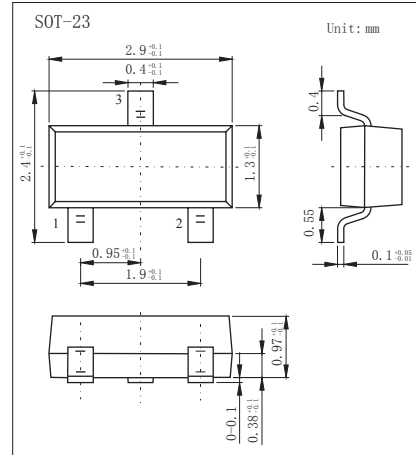
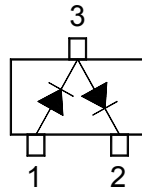


SOT-23 Plastic-Encapsulate Diodes

BAV99 Switching Diodes

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Repetitive Peak Reverse Voltage	V_{RRM}	100	V	
Continuous Reverse Voltage	V_R	75		
Forward Current (Double Diode Loaded)	I_F	125	mA	
Forward Current (Single Diode Loaded)		215		
Repetitive Peak Forward Current	I_{FRM}	450		
Non-repetitive Peak Forward Surge Current	I_{FSM}	$t=1s$	0.5	A
		$t=1ms$	1	
		$t=1\mu s$	1.5	
Power Dissipation	P_d	350	mW	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature range	T_{stg}	-65 to 150		

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	100			V
Forward voltage	V_F	$I_F = 1 \text{ mA}$			0.715	
		$I_F = 10 \text{ mA}$			0.855	
		$I_F = 50 \text{ mA}$			1	
		$I_F = 150 \text{ mA}$			1.25	
Reverse voltage leakage current	I_R	$V_R = 25 \text{ V}$			30	nA
		$V_R = 75 \text{ V}$			1	uA
		$V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$			30	
		$V_R = 75 \text{ V}, T_J = 150^\circ\text{C}$			50	
Junction capacitance	C_j	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10 \text{ mA}, I_R = 1 \text{ mA}, R_L = 100 \Omega$			4	ns

■ Marking

Marking	A7*
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■ Typical Characteristics

